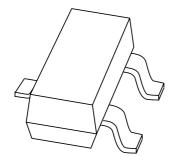
DISCRETE SEMICONDUCTORS

DATA SHEET



BAV74High-speed double diode

Product data sheet Supersedes data of 1999 May 11 2004 Jan 14



High-speed double diode

BAV74

FEATURES

- Small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 50 V
- Repetitive peak reverse voltage: max. 60 V
- Repetitive peak forward current: max. 450 mA.

APPLICATIONS

• High-speed switching in thick and thin-film circuits.

DESCRIPTION

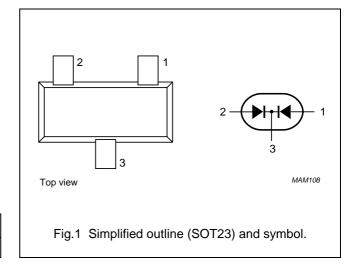
The BAV74 consists of two high-speed switching diodes with common cathodes, fabricated in planar technology, and encapsulated in a small SOT23 plastic SMD package.

MARKING

TYPE NUMBER	MARKING CODE(1)
BAV74	JA*

PINNING

PIN	DESCRIPTION
1	anode (a1)
2	anode (a2)
3	cathode



Note

- * = p : Made in Hong Kong.
 - * = t : Made in Malaysia.
 - * = W: Made in China.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V _{RRM}	repetitive peak reverse voltage		_	60	V
V _R	continuous reverse voltage		_	50	V
I _F	continuous forward current	single diode loaded; note 1; see Fig.2	_	215	mA
		double diode loaded; note 1; see Fig.2	_	125	mA
I _{FRM}	repetitive peak forward current		_	450	mA
I _{FSM}	non-repetitive peak forward	square wave; T _j = 25 °C prior to surge; see Fig.4			
	current	t = 1 μs	_	4	Α
		t = 1 ms	_	1	Α
		t = 1 s	_	0.5	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C

Note

1. Device mounted on an FR4 printed-circuit board.

High-speed double diode

BAV74

ORDERING INFORMATION

TYPE NUMBER	PACKAGE			
TIPE NOMBER	NAME	DESCRIPTION	VERSION	
BAV74	_	plastic surface mounted package; 3 leads	SOT23	

ELECTRICAL CHARACTERISTICS

 $T_i = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
Per diode				
V _F	forward voltage	see Fig.3		
		$I_F = 1 \text{ mA}$	715	mV
		I _F = 10 mA	855	mV
		I _F = 100 mA	1.0	V
I _R	reverse current	see Fig.5		
		V _R = 25 V	30	nA
		V _R = 50 V	0.1	μΑ
		V _R = 25 V; T _j = 150 °C	30	μΑ
		$V_R = 50 \text{ V}; T_j = 150 ^{\circ}\text{C}$	100	μΑ
C _d	diode capacitance	f = 1 MHz; V _R = 0; see Fig.6	1.5	pF
t _{rr}	reverse recovery time	when switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100$ Ω ; measured	4	ns
		at $I_R = 1$ mA; see Fig.7		
V _{fr}	forward recovery voltage	when switched from $I_F = 10$ mA; $t_r = 20$ ns; see Fig.8	1.75	V

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-tp)}	thermal resistance from junction to tie-point		360	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W

Note

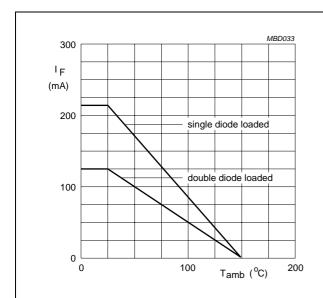
1. Device mounted on an FR4 printed-circuit board.

Product data sheet **NXP Semiconductors**

High-speed double diode

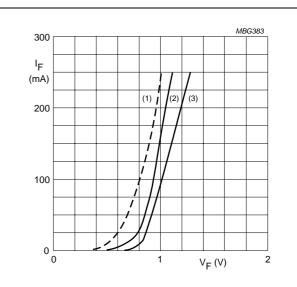
BAV74

GRAPHICAL DATA



Device mounted on an FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



- (1) $T_j = 150 \,^{\circ}\text{C}$; typical values.
- (2) $T_j = 25$ °C; typical values.
- (3) T_j = 25 °C; maximum values.

Fig.3 Forward current as a function of forward voltage.

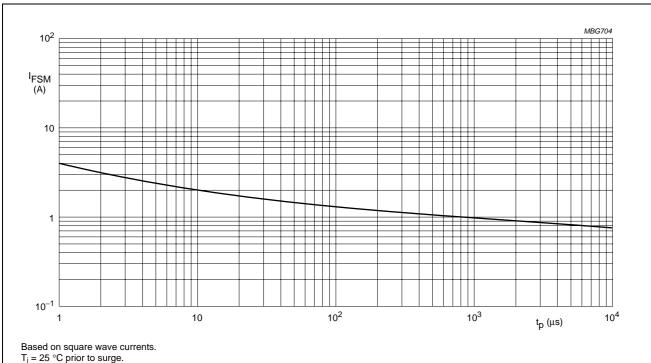
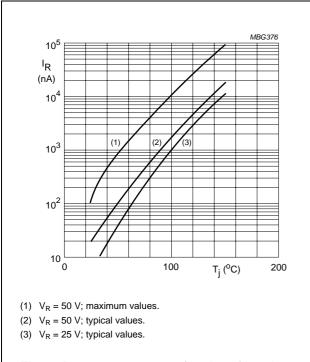


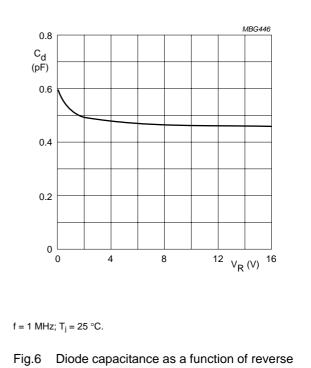
Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

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High-speed double diode

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voltage; typical values.

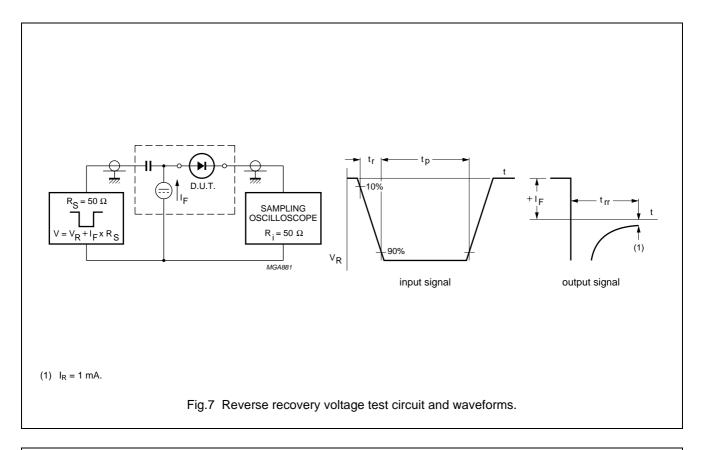
Fig.5 Reverse current as a function of junction temperature.

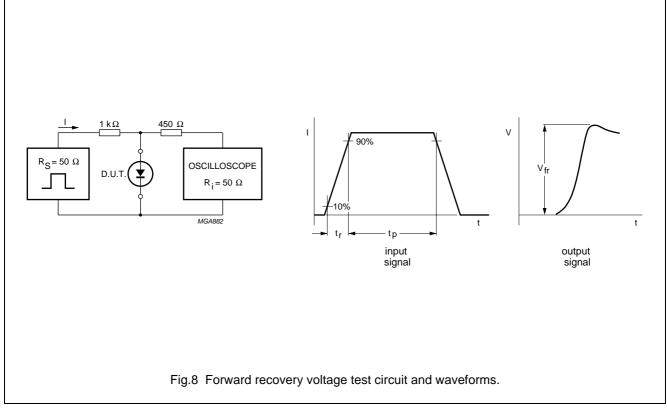
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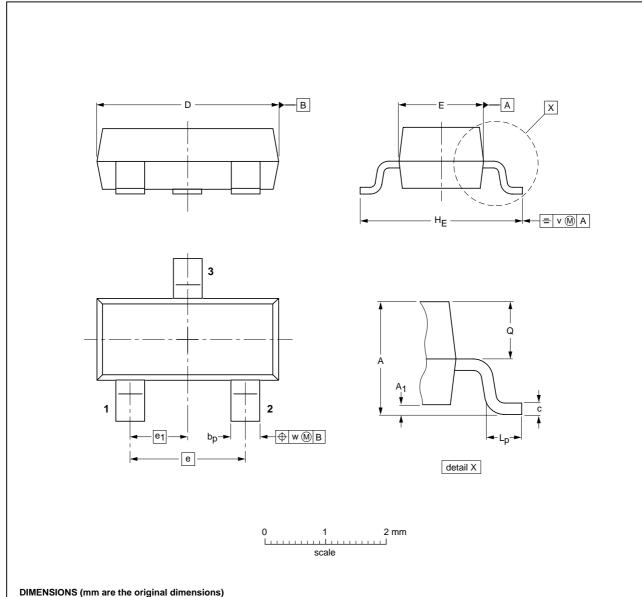
High-speed double diode

BAV74

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



DIMENS	ЮИЗ (П	ım are tı	ne origir	nai dime	nsions)	

UNIT	Α	A ₁ max.	bp	С	D	E	е	e ₁	HE	Lp	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEDEC JEITA PROJECTION		ISSUE DATE	
SOT23		TO-236AB				-04-11-04 06-03-16

High-speed double diode

BAV74

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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